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10/743,073	12/23/2003	Takashi Ichimori	2003-1815A	7424
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WENDEROTH, LIND & PONACK, L.L.P.			MONDT, JOHANNES P	
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SUITE 800			PAPER NUMBER	
WASHINGTON, DC 20006-1021			2826	

DATE MAILED: 08/08/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

## Office Action Summary

Application No.

10/743,073

Applicant(s)

ICHIMORI, TAKASHI

Examiner

Johannes P. Mondt

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☒ Responsive to communication(s) filed on 31 May 2005.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-13 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-13 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

### Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some \* c) ☐ None of:
- 1) ☒ Certified copies of the priority documents have been received.
  - 2) ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  - 3) ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.

### Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Response to Amendment*

Amendment filed 5/31/05 forms the basis of this office action. In said Amendment Applicant substantially amended all pending claims 1-13.

Comments on Remarks in said Amendment are included below under "Response to Arguments".

### ***Claim Rejections - 35 USC § 103***

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. ***Claims 1, 4, 6, 8, 9, 10, 12 and 13*** are rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al (US 2002/0074601 A1) in view of the Prior Art as Admitted by Applicant, or, in the alternative, in view of Kanaya et al (6,611,014 B1). *Fox et al teach a method of manufacturing a ferroelectric device* (see title) comprising steps of:

providing a substrate 100 on IC circuit wafer (hence semiconductor substrate)(par. [0039]);

forming a multi-layer body by depositing successively a contact film 102 ([0038]), a lower electrode 104 ([0039]), a ferroelectric film 106/108 ([0040]) and an upper electrode 110 ([0044]) on said substrate; and processing said multi-layer body (steps 300 and 404; see Figure 4 and [0053]-[0056]), wherein said processing step comprises:

etching (step 300) said upper electrode and said ferroelectric film (Figure 4 and [0053]);

heat treatment step 402 (Figure 4 and [0055]; see also the equivalent step 208 as described in [0041]) said ferroelectric film in an oxidizing atmosphere ([0015]) under a condition wherein said contact film is covered with said lower electrode; and

etching (step 404; Figure 4 and [0056]) said lower electrode.

*Fox et al do not necessarily teach the further limitation that said second etching step also etches said contact film 102, thereby exposing said insulating substrate 100. However, it would have been obvious to include said further limitation in view of Prior Art as Admitted by Applicant, or, in the alternative, in view of Kanaya et al: said Prior Art as Admitted by Applicant teaches that the second etching step etches not only the lower electrode but also the contact film (see page 3; and see page 4 for the definition of contact film to include any binding film); with regard to the alternative rejection, Kanaya et al teach the second step to etch the contact film 301 (col. 8, l. 42-58 and col. 11, l. 60-64: it is noted that the hydrogen barrier layer, be it 101 or 301, is an adhesive layer and thus meets the definition of contact layer in the Specification, page 4).*

*Motivation* to include the teaching by the Prior Art as Admitted by Applicant, or, in the alternative, the teaching by Kanaya et al, at least derives from the function of said contact layer, as a layer to make contact with the lower electrode: in the locations where said lower electrode is absent there also is no need for said contact layer. Thus a more functionally focused device is achieved.

*On claim 4:* said method by Fox et al includes forming a first cover film (masking film) so as to cover said upper electrode, ferroelectric film and lower electrode and etching said first cover film together with said multi-layer body (Figure 4 and [0056]), and wherein said forming of the first cover film is performed before said etching of said lower electrode and said contact film ([0058]).

*On claim 6:* although Fox et al do not necessarily teach the further limitation defined by claim 6 it would have been obvious to include it as part of a conventional method of etching in view of Kanaya et al, who teach the use of hard mask 34 on the upper electrode 5 (Figure 61) in preparation of the etching step of the lower electrode area, which comprises the contact film area (see col. 24, l. 22-32). Motivation to include the teaching by Kanaya et al in this regard derives from the need to delimit the area that needs to be etched, for which said hard mask serves in a conventional manner.

*On claim 8:* the method by Fox et al further comprises a step 218 for forming a second cover film 112 ([0049] and [0056] and Figure 4) so as to cover said multi-layer body after said etching of said lower electrode and contact film.

*On claim 9:* the method by Fox et al further comprises heat treating (step 406) ([0056] and Figure 4) said ferroelectric film after said second cover film.

*On claim 10:* the contact film 102 of the method by Fox et al includes a binding film 102 ([0038] and Figure 4).

*On claim 12:* said heat treating in Fox et al is performed to recover a crystalline structure in the ferroelectric film ([0041], [0051] and [0055]).

*On claim 13:* said heat treating of said ferroelectric film in Fox et al and as claimed here in claim 9 is performed to recover a crystalline structure in the ferroelectric film after said forming of the second cover film ([0016])(step 502: see [0060] and Figures 4-5); see also the patent cited and incorporated by reference in Fox et al in this regard), while furthermore the additional heat treatment (anneal) inherently causes further crystallization unless crystallization is perfect to start with, which obviously is not expected by overwhelming probability against it.

3. **Claim 2** is rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al and either Prior Art as Admitted by Applicant or, in the alternative, over Fox et al and Kanaya et al as applied to claim 1 above, and further in view of Jung et al (JP 2001-044377, IDS item AJ). *Fox et al teach* an insulating film (titanium oxide) 100 disposed on said substrate that is a semiconductor substrate having a transistor ([0038]) (i.e., "CMOS integrated circuit wafer"). *Fox et al do not necessarily teach* the further limitation that a contact plug to be formed so as to electrically connect said transistor to said contact film. *However, it would have been obvious to include said further limitation in view of Jung et al*, who, in a patent publication on a ferroelectric capacitor for a transistor, hence analogous art, teach a contact plug 114 formed so as to pass through said insulating film 108/112 and electrically connect the transistor (with gate 104 and source/drain regions 106) with said contact film (through its un-etched sides). *Motivation* to include the teaching in this regard by Jung et al in the invention by Fox et al derives from the obvious applicability of the invention by Fox to those FRAM embodiments wherein the electrical connection between the drain region of the transistors of the

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CMOS integrated circuit and the ferroelectric capacitor is achieved through the insulating substrate over the CMOS wafer, i.e., through the shortest route possible, thus saving ohmic dissipation and material investment.

4. **Claim 3** is rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al in view of Prior Art as Admitted by Applicant. As detailed above, claim 1 is unpatentable inter alia over Fox et al in view of Prior Art as Admitted by Applicant. Furthermore, in the first etching step in the Prior Art as Admitted by Applicant the lower electrode is partly etched in said etching of said upper electrode and said ferroelectric film so as to arrive at a predetermined thickness of the lower electrode. *Motivation* to include the teaching in this regard by Prior Art as Admitted by Applicant at least derives from the implied means to set the thickness of the lower electrode.

5. **Claim 5** is rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al and the Prior Art as Admitted by Applicant, or, in the alternative, over Fox et al and Kanaya et al as applied to claim 4 above, and further in view of Kim et al (US 2002/0053690 A1). Although Fox et al, the Prior Art as Admitted by Applicant, nor Kanaya necessarily teach the further limitation defined by claim 5, it would have been obvious to include said further limitation in view of Kim et al, who, in a patent on a semiconductor memory device with capacitor, - hence analogous art (title, abstract), teach the etching step, for the lower electrode contact hole to be performed in a self-alignment manner ([0074]). *Motivation* to include teaching by Kim et al derives from superior alignment.

6. **Claim 7** is rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al and the Prior Art as Admitted by Applicant, or, in the alternative: over Fox et al and Kanaya et al as applied to claim 4 above, and further in view of Ohyagi (US 2003/0211685 A1). Although neither Fox et al nor the Prior Art as Admitted by Applicant nor Kanaya et al necessarily teach the further limitation defined by claim 7, it would have been obvious to include said further limitation in view of Ohyagi, who, in a patent application drawn to a FeRAM device (title, abstract and [0003]), hence analogous art, teach to use resist as mask pattern for an etching step so as not to etch more than the area selected for etching (see [0023]). Motivation to include the teaching by Ohyagi in the invention by Fox et al derives from the need to accurately select a particular surface area for etching.

7. **Claim 11** is rejected under 35 U.S.C. 103(a) as being unpatentable over Fox et al and Prior Art as Admitted by Applicant, or, in the alternative, over Fox et al and Kanaya et al as applied to claim 10 above, and further in view of Nagano et al (US 2002/0195633 A1). As detailed above claim 10 is unpatentable over Fox et al in view of either Prior Art as Admitted by Applicant or Kanaya et al. Neither Fox et al, nor Prior Art as Admitted by Applicant, - nor Kanaya et al, necessarily teach the further limitation of the contact film to include an oxidation barrier film. However, it would have been obvious to include said further limitation in view of Nagano et al, who, in a patent on a ferroelectric capacitor for a semiconductor memory device (title, abstract, [0004], [0104]), - hence analogous art, teach the inclusion of an iridium oxide ( $\text{IrO}_2$ ) oxygen barrier film 31, as well as an iridium (Ir) oxygen barrier film between a platinum (Pt)

lower electrode and the substrate so as to prevent the cross-layer diffusion of oxygen (Figure 1B, abstract, [0013] and [0103]). *Motivation* to include the teaching in this regard by Nagano et al in the invention by Fox et al derives from the deleterious effect of oxygen diffusion to contact plugs in ferroelectric capacitor semiconductor devices. The teaching can be *combined* with the invention because the material constitution of the layers (oxide substrate 45 ([0179]), platinum lower electrode 31d ([0103]) and lead zirconate titanate (PZT) (inter alia) ([0185]) and the generally metallic constitution of the contact plug to be protected against oxidation, imply the same conditions for oxygen diffusion, thus requiring the same measures.

### ***Response to Arguments***

8. Applicant's arguments filed 5/31/05 have been fully considered but they are not persuasive. In particular, although the grounds for objection to the specification and the rejections under 35 USC 112, second paragraph, have been removed by amendment to the claims stand rejected because counter to Applicant's allegation based on paragraph [0041], Fox et al do teach said heat treating (anneal) of the ferroelectric film to take place in an oxygen atmosphere, namely an atmosphere containing 5% oxygen (see full text of paragraph [0041]). All other arguments of traverse appear to depend on the one discussed above. All claims have, furthermore, substantially been amended and therefore all rejections are being offered at the earliest time possible.

### ***Conclusion***

9. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP

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§ 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Johannes P. Mondt whose telephone number is 571-272-1919. The examiner can normally be reached on 8:00 - 18:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J. Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JPM  
July 26, 2005



**EVAN PERT**  
**PRIMARY EXAMINER**